

## Substantially Enhancing Quantum Coherence of Electrons in Graphene via Electron-Plasmon Coupling

Guanghai Cheng,<sup>1,2</sup> Wei Qin,<sup>1</sup> Meng-Hsien Lin,<sup>3</sup> Laiming Wei,<sup>1,2,†</sup> Xiaodong Fan,<sup>1,2</sup> Huayang Zhang,<sup>1,2</sup> Shangjr Gwo,<sup>3,4</sup> Changgan Zeng,<sup>1,2,\*</sup> J. G. Hou,<sup>1</sup> and Zhenyu Zhang<sup>1</sup>

<sup>1</sup>International Center for Quantum Design of Functional Materials (ICQD),

Hefei National Laboratory for Physical Sciences at the Microscale,  
and Synergetic Innovation Center of Quantum Information and Quantum Physics,  
University of Science and Technology of China, Hefei, Anhui 230026, China

<sup>2</sup>CAS Key Laboratory of Strongly-Coupled Quantum Matter Physics, and Department of Physics,  
University of Science and Technology of China, Hefei, Anhui 230026, China

<sup>3</sup>Department of Physics, National Tsing-Hua University, Hsinchu 30013, Taiwan

<sup>4</sup>National Synchrotron Radiation Research Center, Hsinchu 30076, Taiwan

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The interplays between different quasiparticles in solids lay the foundation for a wide spectrum of intriguing quantum effects, yet how the collective plasmon excitations affect the quantum transport of electrons remains largely unexplored. Here we provide the first demonstration that when the electron-plasmon coupling is introduced, the quantum coherence of electrons in graphene is substantially enhanced with the quantum coherence length almost tripled. We further develop a microscopic model to interpret the striking observations, emphasizing the vital role of the graphene plasmons in suppressing electron-electron dephasing. The novel and transformative concept of plasmon-enhanced quantum coherence sheds new insight into interquasiparticle interactions, and further extends a new dimension to exploit nontrivial quantum phenomena and devices in solid systems.

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When electrons move in solids, they interact with other diversified quasiparticles, and these essential many-body couplings modify the behaviors of electrons substantially. For example, phonon or spin fluctuation mediated electron pairing leads to superconductivity [1–3]. Polarons protect carriers from scattering with charged defects and optical phonons in hybrid organic-inorganic perovskites [4]. Plasmons, the harmonic oscillations of conduction electrons with a coherent phase, may also affect the quantum behavior of electrons. In particular, it has been revealed that the electron-plasmon coupling results in the formation of a new composite quasiparticle, i.e., plasmaron [5–7]. Nevertheless, how plasmon excitations tune the quantum transport of electrons in solids still remains to be established.

On the other hand, it was found that quantum entanglement survives during photon-plasmon-photon conversion [8,9], which strongly suggests that the quantum nature of the plasmons ensures high quantum fidelity even though a single plasmon mode already involves a massive number of electrons [8,10]. A natural question arises: Will plasmons affect the quantum behaviors of electrons in a conceptually similar, or different, manner? Here we exploit the weak localization effect in graphene [11,12], a direct measure of the constructive quantum interference of the electrons [11–14], to address this fundamental issue, and discover that electron-plasmon coupling can indeed improve the coherent quantum characteristics in graphene substantially.

Plasmons cannot be directly excited in a pristine graphene sheet by far-field light illumination due to momentum mismatch [15]. In the present study, plasmons were instead induced in graphene by nanocavity coupling [16–21] from proximal Au nanoparticles (AuNPs) synthesized using an established approach [22] (see more details in Secs. I and IIIA of Supplemental Material (SM) [23]). The AuNPs/Al<sub>2</sub>O<sub>3</sub>/graphene devices were then fabricated as depicted in Fig. 1. The Al<sub>2</sub>O<sub>3</sub> layer is about 2 nm thick to prevent charge transfer [39] between the AuNPs and graphene. Figure 1(d) shows the optical absorption spectra of the AuNPs, and a strong plasmon resonance is featured at ~550 nm.

Next we study how the plasmon excitation in the AuNPs manipulates the quantum transport in graphene. Figure 2(a) displays the relative conductivity [ $\Delta\sigma = \sigma(B) - \sigma(0)$ ] of graphene as a function of magnetic field ( $B$ ) at temperature ( $T$ ) of 1.5 K and gate voltage of 10 V, under laser illumination with a wavelength of 532 nm close to the AuNP plasmon resonance. Weak localization effect manifested as a dip around zero field in the  $\Delta\sigma$ - $B$  curve [40–42] is featured for all the cases, arising from the constructive quantum interference of electron waves, which is gradually suppressed by the magnetic field (see more descriptions in Sec. IIA of SM [23]). Strikingly, compared to the case without illumination, the weak localization magnitude rises when the illumination is on and further increases drastically with increasing illumination power ( $P$ ).

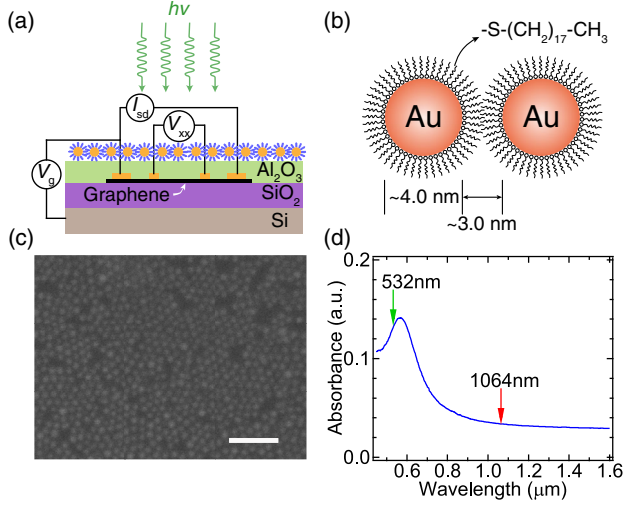


FIG. 1. Device schematics and characterizations. (a) Schematic of the AuNPs/Al<sub>2</sub>O<sub>3</sub>/graphene device used in the transport measurements under laser illumination. (b) Schematic of the AuNPs capped with 1-octadecanethiolate protection layer. (c) Scanning electron microscope image of a representative device. The scale bar is 40 nm. (d) Optical absorption spectra of the AuNPs on a quartz substrate.

We then discuss the likely mechanisms leading to such drastically enhanced weak localization effect. It could be induced by changes in the carrier density ( $n$ ) and mobility ( $\mu$ ) of graphene [40,41] upon illumination. However, the variations of  $n$  and  $\mu$  in response to laser illumination are too weak [ $<4\%$  as shown in Fig. 2(b)] to account for the giant increase of the weak localization magnitude. Another possibility might be attributed to the effect of the applied electromagnetic field on the graphene. However, such a field effect was revealed to offer an additional dephasing channel to suppress weak localization [43–45]. A third possible factor could be the overheating of graphene electrons caused by the illumination. However, if such a thermal effect played a dominant role, the weak localization magnitude would decrease with increasing laser power [13,46], contrary to the revealed behaviors.

Based on the discussions above, the enhanced weak localization effect in graphene can most probably be attributed to the effect of the plasmon excitations in the proximal AuNPs. To further validate the plasmonic origin, magnetotransport was further performed under illumination with different wavelengths but the same photon flux. For 532-nm illumination, weak localization is enhanced notably and returns to the initial state after removal of the illumination [Fig. 2(c)]. This suggests that the weak localization enhancement is a pure electronic effect without irreversible atomic reconstruction. In sharp contrast, the weak localization under 1064-nm illumination is almost the same as that without illumination [Fig. 2(d)], which can be attributed to the fact that this wavelength is far away from the AuNP plasmon resonance. Moreover, no weak

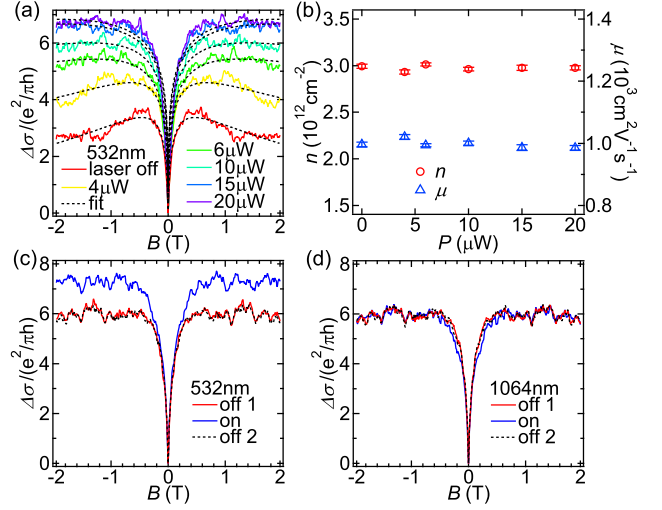


FIG. 2. Enhanced weak localization effect by plasmon excitation. (a) Relative conductivity  $\Delta\sigma = \sigma(B) - \sigma(0)$  as a function of the magnetic field  $B$  for a specific device under 532-nm illumination with various powers. The dashed curves are the weak localization fittings. (b) Carrier density  $n$  and mobility  $\mu$  versus laser power  $P$ . (c)  $\Delta\sigma$  as a function of  $B$  for another device within an off-on-off cycle of 532-nm illumination. (d)  $\Delta\sigma$  as a function of  $B$  within an off-on-off cycle of 1064-nm illumination. The photon flux in (c) and (d) is the same ( $\sim 1 \times 10^{11} \text{ s}^{-1} \text{ mm}^{-2}$ ).

localization enhancement is observed for the bare Al<sub>2</sub>O<sub>3</sub>/graphene/SiO<sub>2</sub>/Si or graphene/SiO<sub>2</sub>/Si samples under 532-nm illumination (see Fig. S2 in SM [23]). These control experiments confirm unambiguously that the enhanced weak localization effect in graphene must arise from the plasmonic effect of the proximal AuNPs.

Because the weak localization magnitude is largely determined by the phase coherence length [13,47], our observation strongly suggests that the quantum coherence in the graphene in proximity to the AuNPs is drastically enhanced under laser illumination. To quantitatively characterize this effect, the measured magnetoconductivities in Fig. 2(a) were fitted using the well-established formalism adopted to describe weak localization effects in graphene [11,40,42],

$$\Delta\sigma(B) = \frac{e^2}{\pi h} \left[ F\left(\frac{B}{B_\phi}\right) - F\left(\frac{B}{B_\phi + 2B_i}\right) - 2F\left(\frac{B}{B_\phi + B_i + B_*}\right) \right],$$

where  $F(z) = \ln(z) + \Psi(1/2 + z^{-1})$ ,  $\Psi(x)$  is the digamma function, and  $B_{\phi,i,*} = \hbar/(4eL_{\phi,i,*}^2)$ . Here  $L_\phi$  is the phase coherence length above which the coherence is lost due to inelastic scatterings,  $L_i$  the elastic intervalley scattering length, and  $L_*$  the elastic intravalley scattering length. The dephasing rate ( $\tau_\phi^{-1}$ ) can be extracted from the relation  $\tau_\phi^{-1} = D/L_\phi^2$ , where  $D = V_F^2 \tau_{tr}/2$  denotes the diffusion

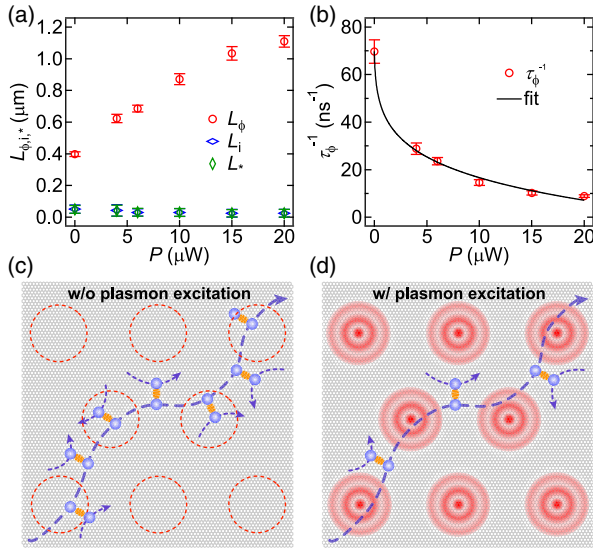


FIG. 3. Plasmon-enhanced quantum coherence and the mechanism. (a) Phase coherence length  $L_\phi$ , elastic intervalley scattering length  $L_i$ , and elastic intravalley scattering length  $L_*$  as functions of 532-nm laser power  $P$ , extracted from the weak localization fittings in Fig. 2(a). (b) Extracted dephasing rate  $\tau_\phi^{-1}$  as a function of  $P$ . The black curve is the fitting based on the phenomenological model described in Sec. III of SM [23]. (c) Schematic of an electron trajectory (blue curve) in graphene without plasmon excitation. The pairs of blue balls with yellow ties represent inelastic electron-electron scattering events that break the phase coherence. The red dotted circles indicate the unexcited plasmon domains underneath the AuNPs. (d) Schematic of an electron trajectory with plasmon excitation. The red shaded concentric circles are domains of plasmon excitation, in which the inelastic scattering is suppressed.

coefficient,  $V_F \approx 1.1 \times 10^6$  m/s the Fermi velocity [48,49], and  $\tau_{tr} = \mu\hbar\sqrt{\pi n}/(eV_F)$  the momentum relaxation time.

As displayed in Fig. 2(a), the weak localization data can be well fitted within this formalism. The derived  $L_\phi$ ,  $L_i$ ,  $L_*$ , and  $\tau_\phi^{-1}$  as functions of  $P$  are plotted in Figs. 3(a) and 3(b), respectively. It is evident that  $L_\phi$  ( $\tau_\phi^{-1}$ ) rises (drops) dramatically with increasing  $P$ , with  $L_\phi$  varying from  $\sim 400$  nm at  $0 \mu\text{W}$  to  $\sim 1100$  nm at  $20 \mu\text{W}$ . Meanwhile,  $L_i$  decreases from  $\sim 50$  to  $\sim 25$  nm. Although the enhanced intervalley scattering may contribute to the weak localization enhancement [11,50,51], the increase in  $L_\phi$  plays a critical role in enhancing the weak localization under resonant illumination, as detailed in Sec. IIB of SM [23].

It is noted that the universal conductance fluctuations (UCF), manifested as reproducible fluctuations in the  $\Delta\sigma$ - $B$  curves [12,40], do not show a clear increasing amplitude upon increasing the illumination power (see Fig. 2 and Fig. S4 in SM [23]). As detailed in Sec. IIC of SM [23], the UCF magnitude in the present case depends not only on  $L_\phi$ , but also on the thermal length  $L_T$ ,  $L_i$ , and  $L_*$  [52–55]. Qualitatively, the decrease in  $L_i$ ,  $L_*$ , and  $L_T$  upon resonant illumination would suppress the UCF [52–55]; therefore,

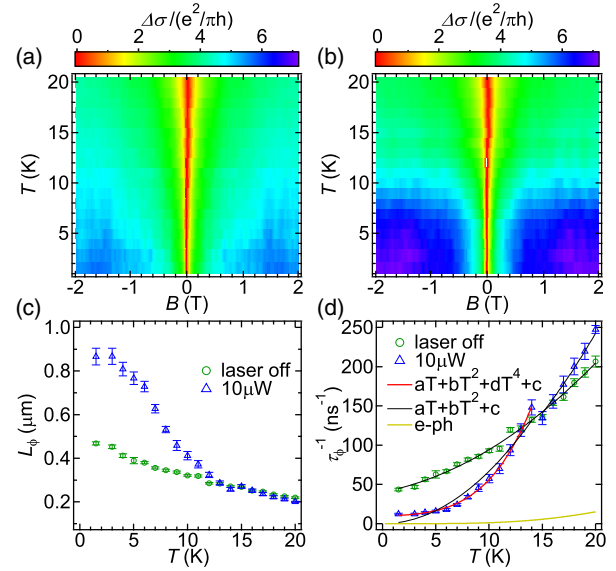


FIG. 4. Temperature dependence of plasmon-enhanced quantum coherence. (a)  $T$ -dependent weak localization effect for a third device without illumination. (b)  $T$ -dependent weak localization effect with 532-nm laser illumination. (c) Extracted phase coherence length  $L_\phi$  as a function of  $T$  without and with 532-nm illumination. (d) Extracted dephasing rate  $\tau_\phi^{-1}$  as a function of  $T$ . Fittings and calculation by adopting various models are also shown.

the increase in  $L_\phi$  may not necessarily lead to a clear enhancement in the UCF magnitude.

The dependence of the plasmonic origin on temperature is further exploited in the low-temperature regime without and with 532-nm illumination, respectively, as shown in Figs. 4(a) and 4(b). It is evident that the enhancement of quantum coherence disappears above 13 K, which is more obvious from the derived  $T$ -dependent  $L_\phi$  and  $\tau_\phi^{-1}$  as displayed in Figs. 4(c) and 4(d).

The dominant dephasing mechanism can be inferred from the  $T$  dependence of  $\tau_\phi^{-1}$  [13,40–42,56]. As revealed in Fig. 4(d), in the absence of plasmon excitation,  $\tau_\phi^{-1}(T)$  can be well fitted by the conventional electron-electron dephasing mechanism [40,42],  $\tau_\phi^{-1}(T) = aT + bT^2 + c$ , where the first term arises from the interaction of an electron with the fluctuating electromagnetic field induced by the noisy movement of the neighboring electrons (Nyquist dephasing) [40], while the second term arises from the direct Coulomb interaction of the electrons [40] with  $a$ ,  $b$ , and  $c$  as constants. Meanwhile, the electron-phonon scattering rate ( $\tau_{e-ph}^{-1}$ ) estimated from the model based on the Boltzmann transport theory [57,58] is much smaller than the experimentally derived  $\tau_\phi^{-1}$ . These results demonstrate that electron-electron scattering is the dominant dephasing mechanism in graphene at low temperature, consistent with previous studies [40,41,59].

In the presence of plasmon excitations in the proximal AuNPs, the electron-electron dephasing picture can still fit

the  $\tau_\phi^{-1}(T)$  behavior above 14 K. However, this picture fails to describe the  $\tau_\phi^{-1}(T)$  behavior below 14 K as revealed in Fig. 4(d). Rather, the low-temperature behavior is better fitted if an additional  $T^4$  term is taken into account [ $\tau_\phi^{-1}(T) = aT + bT^2 + dT^4 + c$ ,  $d$  being another constant]. Such deviations further imply the critical role of plasmon coupling in enhancing quantum coherence, even though this quantum coupling effect is unable to survive at high temperatures (see more discussion in Sec. IV of SM [23]).

A microscopic phenomenological model is therefore proposed to explain the discovered plasmon-enhanced quantum coherence in graphene. With the excitation of AuNPs plasmon under laser illumination, the strong near-field couplings, namely, nanocavity modes [16–21], between the AuNPs and graphene induce plasmon excitations, i.e., simultaneous electron oscillations in graphene under the AuNPs (see more discussion in Sec. IIIA of SM [23]). As a consequence of multichannel damping, the collective plasmon excitations form two-dimensional domains centered at the AuNPs as schematically illustrated in Figs. 3(c) and 3(d). For simplicity without losing the essential physics, we adopt the scheme that the electron-plasmon interaction is mainly responsible for the inelastic scattering events when the electron trajectory passes through the plasmon excitation domains [red shaded regions in Figs. 3(c) and 3(d)], whereas the conventional electron-electron interactions contribute to the inelastic scattering events in other regions. Such a scheme is justified as detailed in Sec. IIID of SM [23]. The total dephasing rate can then be expressed as  $\tau_\phi^{-1} = (1 - \xi)\tau_{e-e}^{-1} + \xi\tau_{e-pl}^{-1}$ , where  $\xi$  ( $\leq 1$ ) denotes the fractional area of the plasmon domains,  $\tau_{e-pl}^{-1}$  the electron-plasmon scattering rate, and  $\tau_{e-e}^{-1}$  the electron-electron scattering rate. As theoretically analyzed in detail in Secs. IIIB and IIIC of SM [23],  $\tau_{e-pl}^{-1}$  is much lower than  $\tau_{e-e}^{-1}$ . Consequently, the total inelastic scattering is effectively suppressed, leading to the enhancement of quantum coherence.

At a deeper level, plasmons as the collective excitations of electrons arise from the long-range Coulomb interaction of the electrons. Although the estimated lifetime of plasmon in the present system is quite short, the persistent and stable laser illumination drives such a system into a dynamically equilibrium state, where the collective plasmonic excitations can effectively define the steady plasmon domains (see detailed discussion in Sec. IIIC of SM [23]). Furthermore, the excitation of plasmon domains enhances the effectiveness of screening, which in turn largely exhausts the long-range component of the Coulomb interaction. This makes the constituent electrons of plasmon domains invisible for transporting electrons, which consequently reduce the electron-electron scattering rate.

The dependence of the plasmon-enhanced quantum coherence on the illumination power can be well interpreted within this phenomenological model. Under laser illumination, the

size of the plasmon domains gradually increases with increasing  $P$  (see more details in Sec. IIID and Fig. S5 in SM [23]); consequently,  $\tau_\phi^{-1}$  decreases continuously until the plasmon domains cover nearly the whole area of the graphene layer. Figure 3(b) shows that the phenomenological model fits the experimentally obtained  $\tau_\phi^{-1}(P)$  very well (see more details in Sec. IIID of SM [23]).

The present study has demonstrated the vital role of electron-plasmon coupling in enhancing quantum coherence of electrons in solids. This conceptual discovery, in principle, paves the way to the realization of nontrivial quantum effects by tailoring the delicate coupling between quantum quasiparticles. For example, the revealed strong electron-plasmon coupling may eventually stabilize plasmon-mediated superconductivity [60]. Moreover, the drastically enhanced quantum fidelity by electron-plasmon coupling may promise versatile quantum device applications, especially for quantum computing [61].

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G. C., W. Q., and M.-H. L. contributed equally to this work.

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\*Corresponding author.

cgzeng@ustc.edu.cn

†Corresponding author.

laiming@ustc.edu.cn

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